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NX7002BKR-TP

60V N-Channel Mosfet

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Product Summary

- V_{DS} = 60V,I_D = 0.3A

  $R_{DS(ON)}$ < 2.5Ω @ V_{GS}=4.5V

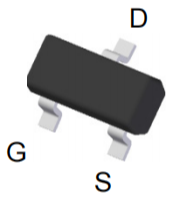
  $R_{DS(ON)}$ < 2.2Ω @ V_{GS}=10V
- ESD Rating : HBM 2000V

Application

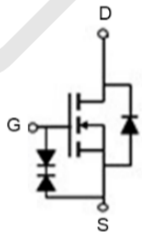
- Direct logic-level interface: TTL/CMOS
- Drivers: relays, solenoids, lamps, hammers,display, memories, transistors, etc.
- Battery operated systems
- Solid-state relays

Package and Pin Configuration

SOT23



Circuit diagram



Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (T_J =150℃)	T_A =25℃	I_D	0.3	A
	T_A =100℃		0.19	
Drain Current-Pulsed (Note 1)		I_{DM}	1.5	A
Maximum Power Dissipation		P_D	0.35	W
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55 To 150	℃

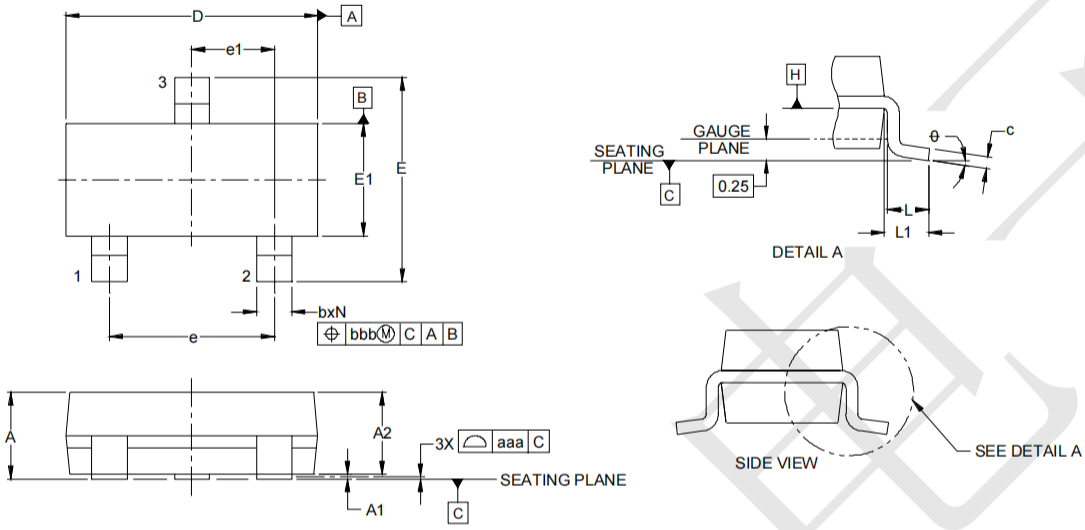
Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	350	℃/W

Electrical Characteristics (T_A = 25°C unless otherwise noted)

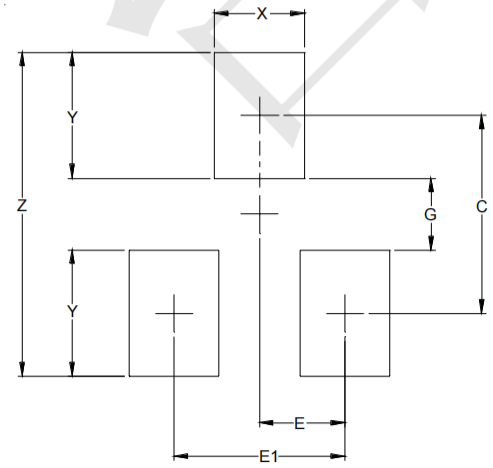
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	60		-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±10V,V_{DS}=0V	-	-	±1	uA
		V_{GS}=±20V,V_{DS}=0V	-		±10	uA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1	1.6		
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D=0.2A	-	1.9	2.5	Ω
		V_{GS}=10V, I_D=0.3A	-	1.8	2.2	Ω
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=0.2A	0.1	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=30V,V_{GS}=0V, F=1.0MHz		27		PF
Output Capacitance	C_{oss}			18		PF
Reverse Transfer Capacitance	C_{rss}			2		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=30V,I_D=0.2A V_{GS}=10V,R_{GEN}=10Ω	-	10	-	nS
Turn-on Rise Time	t_r		-	50	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	17	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	V_{DS}=10V,I_D=0.3A, V_{GS}=4.5V	-	1.7	3	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=0.2A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	0.3	A

SOT23 - Package Outline Drawing



DIM	DIMENSIONS					
	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	.035	-	.044	0.89	-	1.12
A1	.000	-	.004	0.01	-	0.10
A2	.035	.037	.040	0.88	0.95	1.02
b	.012	-	.020	0.30	-	0.51
c	.003	-	.007	0.08	-	0.18
D	.110	.114	.120	2.80	2.90	3.04
E	.082	.093	.104	2.10	2.37	2.64
E1	.047	.051	.055	1.20	1.30	1.40
e	.075			1.90 BSC		
e1	.037			0.95 BSC		
L	.015	.020	.024	0.40	0.50	0.60
L1	.022			(0.55)		
N	3			3		
θ	0°	-	8°	0°	-	8°
aaa	.004			0.10		
bbb	.008			0.20		

Suggested Land Pattern



DIMENSIONS		
DIM	INCHES	MILLIMETERS
C	(.087)	(2.20)
E	.037	0.95
E1	.075	1.90
G	.031	0.80
X	.039	1.00
Y	.055	1.40
Z	.141	3.60